

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application.

**Listing of claims:**

1-6 (Canceled)

7. (Currently Amended) A semiconductor device comprising:
- an ~~active device~~ emitter region provided in a semiconductor substrate facing its principal plane,
  - a body region provided below the emitter region,
  - a drift region provided below the body region,
  - a gate electrode of trench structure, insulated from each of the emitter region, the body region, and the drift region,
  - a field region provided in the semiconductor substrate facing it's principle plane,  
the field region being configured to divide the emitter region and the body region into cells, and
  - a contact electrode provided outside of the semiconductor substrate conducting with the ~~active device~~ emitter region,
  - ~~a P-type body region disposed in the active device,~~
  - ~~a drift region of N-type semiconductor provided below the P-type body region,~~
  - ~~a region of P-type semiconductor provided contacting the drift region and below the drift region, and~~
  - ~~a gate electrode insulated from the semiconductor substrate,~~
  - wherein the emitter region, the body region, and the drift region constitute an insulated gate transistor divided by the field region,
  - the field region is the same conductive type as a portion of the emitter region that contacts with the field region, the field region being low in impurity concentration, and  
~~an end~~ a corner portion of contacting portion of the ~~active device~~ emitter region to

the contact electrode is ~~composed with P-type semiconductor, and a corner of the end portion on the P-type region of the active device is~~ formed with a curved line or with an obtuse angle.

8. (Original) A semiconductor device of claim 7,  
wherein a plurality of active devices are discretely arranged in the semiconductor substrate, and each active device has a contacting portion to a contact electrode, and  
a corner portion of a contacting portion of an active device positioned at the end and at opposite side to another active device is formed with a curved line or with an obtuse angle.

9. (Original) A semiconductor device of claim 7,  
wherein the shape of contacting portion of the active device to the contact electrode is formed in a broader width in an end portion than in the central portion.

10. (Original) A semiconductor device of claim 9,  
wherein a plurality of active devices are discretely arranged in the semiconductor substrate, and each active device has a contacting portion to a contact electrode,  
an end portion of a contacting portion of an active device positioned at an end and at opposite side of another active device is formed broader than the central portion of the contacting portion, and  
a corner portion of the end portion is formed with a curved line or with an obtuse angle.

11. (Currently Amended) A semiconductor device comprising:  
an ~~active device~~ emitter region provided in a semiconductor substrate facing its principal plane,  
a body region provided below the emitter region,  
a drift region provided below the body region,  
a gate electrode of trench structure, insulated from each of the emitter region, the

body region, and the drift region,

a field region provided in the semiconductor substrate facing it's principle plane,  
the field region being configured to divide the emitter region and the body region into  
cells, and

a contact electrode provided outside of the semiconductor substrate conducting  
with the active-device emitter region,

~~a P-type body region disposed in the active device,~~  
~~a drift region of N-type semiconductor provided below the P-type body region,~~  
~~a region of P-type semiconductor provided contacting the drift region and below~~  
~~the drift region, and~~

~~a gate electrode insulated from the semiconductor substrate,~~  
wherein the emitter region, the body region, and the drift region constitute an  
insulated gate transistor divided by the field region,

the field region is the same conductive type as a portion of the emitter region that  
contacts with the field region, the field region being low in impurity concentration, and

~~an end a corner portion of a contacting portion of the active device~~ emitter region  
to contact the contact electrode is ~~composed with P-type semiconductor,~~

~~and has an~~ impurity concentration within the contacting portion that is lower at  
[[a]] the corner portion of the contacting portion than in other portion portions of [[it]] the  
contacting portion.

12. (Original) A semiconductor device of claim 11,

wherein a plurality of active devices are discretely arranged in the semiconductor  
substrate, and each active device has a contacting portion to a contact electrode, and

a corner portion of a contacting portion of an active device positioned at an end  
and at opposite side of another active device is lower in impurity concentration than  
other portion of the contacting portion.